

i don't know why error is coming now A: i found the solution by myself after lots of time i just add my download link in the query string and it works fine
The present invention relates to a method for manufacturing a semiconductor device. More particularly, the invention relates to a method for manufacturing a semiconductor device capable of reducing a resistance of an aluminum wiring layer, a semiconductor device, and an electronic device. An aluminum wiring layer is generally formed in a MOS transistor by a sputtering method, as shown in FIGS. 6(a) and 6(b). In the sputtering method, an aluminum wiring layer 18 is formed in a contact hole 9 formed in an inter-layer insulation layer 20. An inter-layer insulation layer 10 in which the contact hole 9 is formed is formed on the MOS transistor, and a contact plug 12 is formed in the contact hole 9. An aluminum wiring layer 18 is formed in the contact hole 9. The aluminum wiring layer 18 formed in the contact hole 9 is covered with the inter-layer insulation layer 10. An aluminum wiring layer 18 is formed on the inter-layer insulation layer 10 through a barrier metal layer 16. The contact plug 12 is formed in the contact hole 9. The contact plug 12 is connected to a source/drain electrode 14 formed on the MOS transistor. Since a contact resistance between the aluminum wiring layer 18 and the contact plug 12 is large, it is proposed to reduce the contact resistance in the above structure. It is possible to reduce the contact resistance by forming the barrier metal layer 16 of a titanium layer and an aluminum layer in the sputtering method. For example, Japanese Unexamined Patent Publication No. 2003-292338 (paragraphs 0009-0011, FIGS. 1 and 2) discloses a technique of forming a titanium layer and an aluminum layer on the inter-layer insulation layer 20 in a contact hole 9 to reduce the contact resistance. However, if the titanium layer and the aluminum layer are formed in the contact hole 9 by the sputtering method, the titanium layer and the aluminum layer have a high resistance. The resistance of the titanium layer and the aluminum layer reduces an electric current to the source/drain electrode 14, and thus electric current supplied to the source/drain electrode 14 reduces to deteriorate the characteristics of the MOS transistor. In addition, since the aluminum layer and the titanium layer are formed at a high temperature

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... .. - And why would that happen all of a sudden? - Andrew wondered. - And, what was most surprising, it was now. After all, everything was normal. True, I have a suspicion that someone is behind all this, but I'm afraid I can't prove that it is not so. - Are you talking about that strange case which was recently dismissed on the grounds of insufficient evidence? - Yes, that's what I'm talking about. - What's so strange about it? - Well, that the guy we suspected had his car missing at the same time. I don't think he stole it himself. fffad4f19a

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